

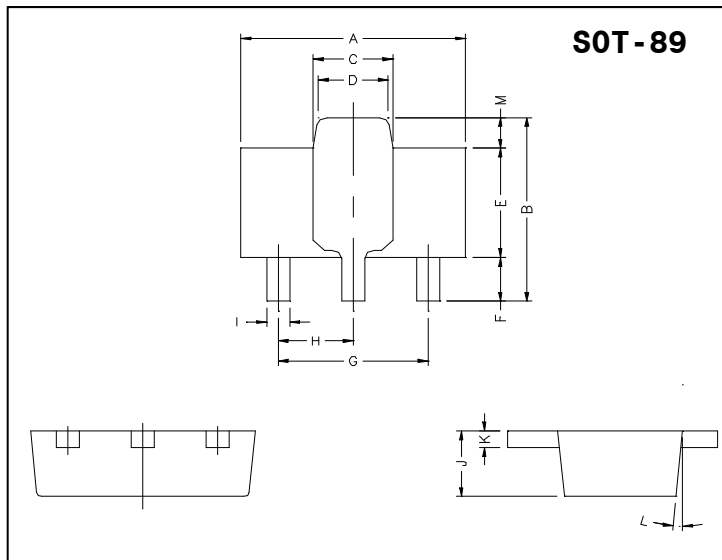
GM6718

NPN EPITAXIAL PLANAR TRANSISTOR

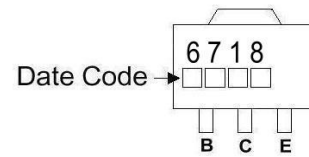
Description

The GM6718 is designed for general purpose medium power amplifier and switching.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

Absolute Maximum Ratings at Ta = 25°C

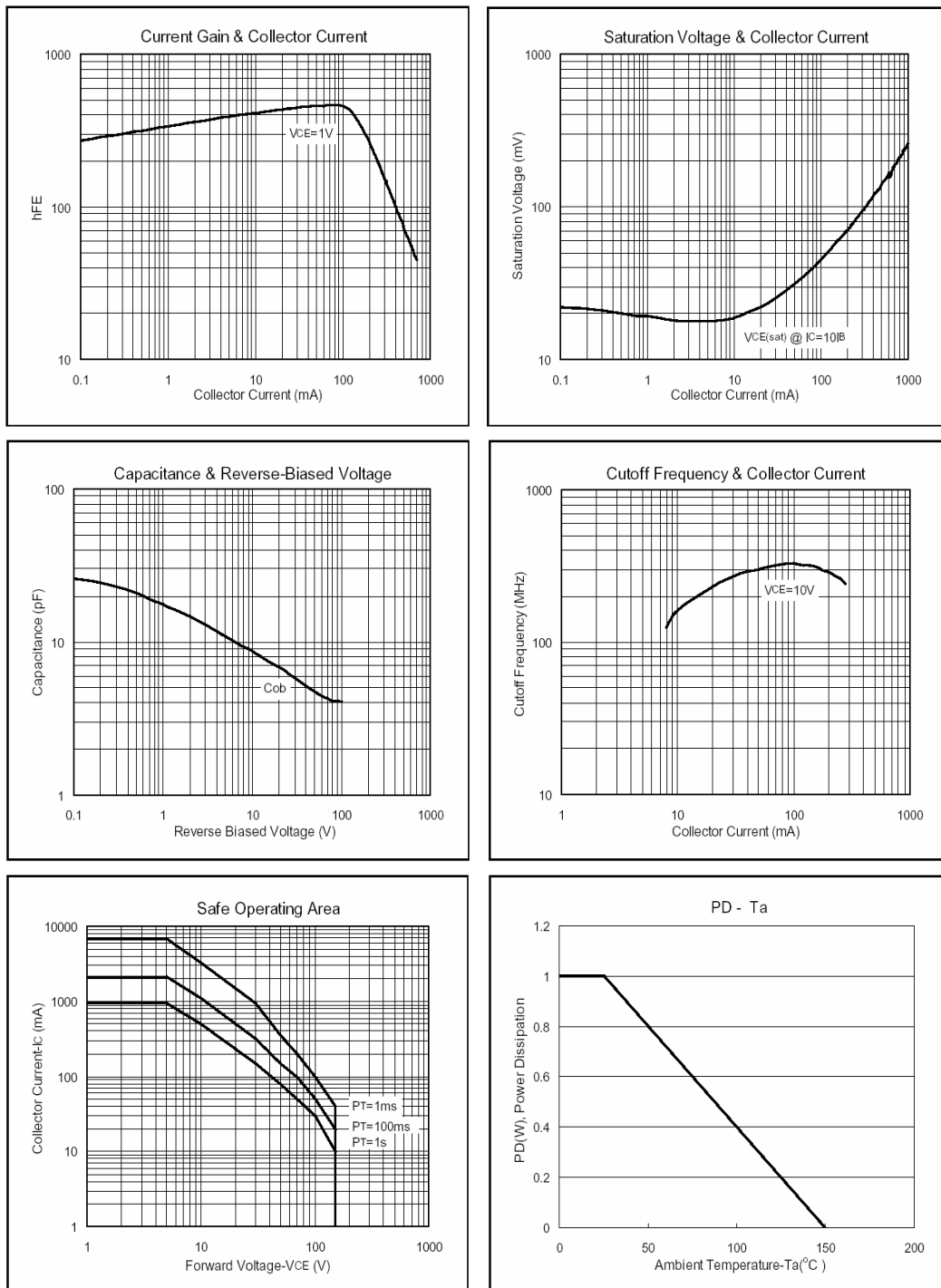
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	100	V
Collector to Emitter Voltage	VCEO	100	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	1	A
Total Power Dissipation	PD	1	W

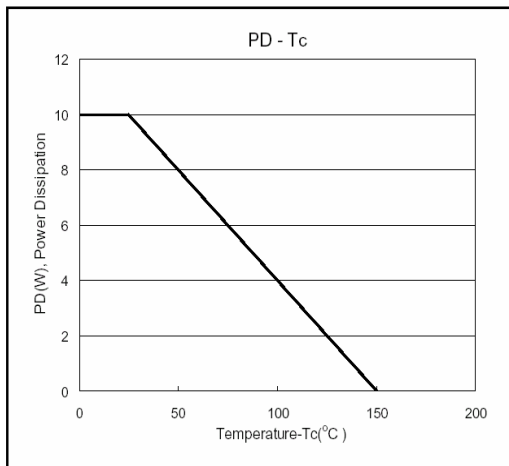
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=100uA, IE=0
BVCEO	100	-	-	V	IC=1mA, IB=0
BVEBO	5	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=80V
*VCE(sat)	-	-	350	mV	IC=350mA, IB=35mA
*hfe1	80	-	-		VCE=1V, IC=50mA
*hfe2	100	-	310		VCE=1V, IC=250mA
*hfe3	20	-	-		VCE=1V, IC=500mA
Cob	-	-	20	pF	VCB=10V, f=1MHz
fT	50	-	-	MHz	VCE=10V, IC=50mA, f=100MHz

*Pulse Test:Pulse width ≤380us,Duty Cycle ≤2%

Characteristics Curve





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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 886-3-597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 FAX : 86-21-38950165